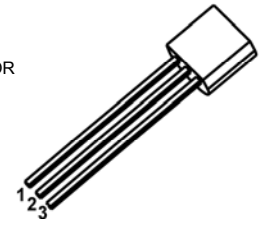
TO-92 Plastic-Encapsulate Transistors

BF421
BF423

TRANSISTOR (PNP)

TO-92

1. EMITTER
2.COLLECTOR
3. BASE



FEATURES

- Low Feedback Capacitance.
- PNP Transistors in a TO-92 Plastic Package.
  NPN Complements: BF420 and BF422
- Class-B Video Output Stages in Colour
  Television and Professional Monitor Equipment.

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	BF421	BF423	Unit
V_{CBO}	Collector-Base Voltage	-300	-250	V
V_{CEO}	Collector-Emitter Voltage	-300	-250	V
V_{EBO}	Emitter-Base Voltage	-5		V
I_C	Collector Current -Continuous	-100		mA
P_C	Collector Power Dissipation	0.83		W
Rth j-a	thermal resistance from junction to ambient	151		℃/W
T_j	junction temperature	150		℃
T_{stg}	Storage Temperature Range	-55~+150		℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter		Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	BF421 BF423	$V_{(BR)CBO}$	I_C=--100μA, I_E=0	-300 -250		V
Collector-emitter breakdown voltage	BF421 BF423	$V_{(BR)CEO}$	I_C= -1mA , I_B=0	-300 -250		V
Emitter-base breakdown voltage		$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5		V
Collector cut-off current		I_{CBO}	V_{CB}=-200 V , I_E=0		-0.01	μA
Emitter cut-off current	BF421 BF423	I_{EBO}	V_{EB}=-5V , I_C=0		-0.1 -0.05	μA
DC current gain		h_{FE}	V_{CE}=-20V, I_C=-25mA	50		
Collector-emitter saturation voltage	BF421 BF423	$V_{CE(sat)}$	I_C=-20mA, I_B=-2mA I_C=-30mA, I_B=-5mA		-0.6	V
Transition frequency		f_T	V_{CE}=-10V, I_C=-10mA f = 100MHz	60		MHz
Feedback capacitance		C_{re}	V_{CE}=-30V,I_C=0,f=1MHz		1.6	pF